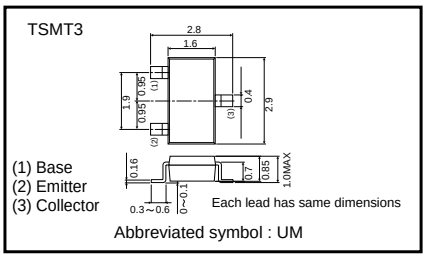
Medium power transistor (30V, 1.0A)

2SC5730

●**Features**

1) High speed switching. (Tf : Typ. : 35ns at I_C = 1.0A)
2) Low saturation voltage, typically
   (Typ. : 150mV at I_C = 500mA, I_B = 50mA)
3) Strong discharge power for inductive load and
   capacitance load.
4) Complements the 2SA2048

●**External dimensions** (Units : mm)



●**Applications**

Small signal low frequency amplifier
High speed switching

●**Structure**

NPN Silicon epitaxial planar transistor

●**Packaging specifications**

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
2SC5730		○

●**Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	1	A
	I_{CP}	2	A *1
Power dissipation	P_C	500	mW *2
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	−55~+150	°C

*1 Pw=10ms
*2 Each terminal mounted on a recommended land.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector–base breakdown voltage	BV_{CBO}	30	–	–	V	I_C=100μA
Collector–emitter breakdown voltage	BV_{CEO}	30	–	–	V	I_C=1mA
Emitter–base breakdown voltage	BV_{EBO}	6	–	–	V	I_E=100μA
Collector cut-off current	I_{CBO}	–	–	1.0	μA	V_{CB}=20V
Emitter cut-off current	I_{EBO}	–	–	1.0	μA	V_{EB}=4V
Collector–emitter staturation voltage	$V_{CE(sat)}$	–	150	300	mV	I_C=500mA, I_B=50mA
DC current gain	h_{FE}	120	–	390	–	V_{CE}=2V, I_C=100mA
Transition frequency	fT	–	270	–	MHz	V_{CE}=10V, I_E= –100mA, f=10MHz*1
Collector output capacitance	Cob	–	10	–	pF	V_{CB}=10V, I_E=0mA,*2 f=1MHz
Turn-on time	Ton	–	30	–	ns	I_C=1A, I_{B1}=0.1A I_{B2}= –0.1A $V_{CC}\simeq$ 25V
Storage time	Tstg	–	120	–	ns	
Fall time	Tf	–	35	–	ns	

*1 Non repetitive pulse
*2 See switching charactaristics measurement cicuits

●h_{FE} RANK

Q	R
120-270	180-390

●Electrical characteristic curves

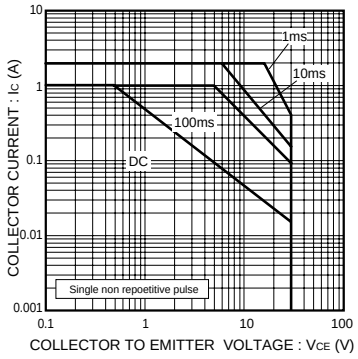


Fig.1 Safe operating area

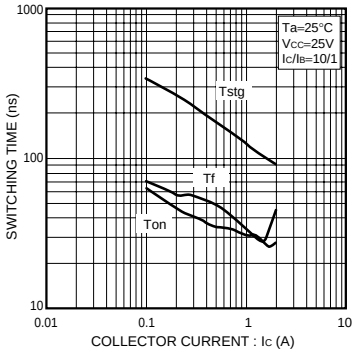


Fig.2 Switching Time

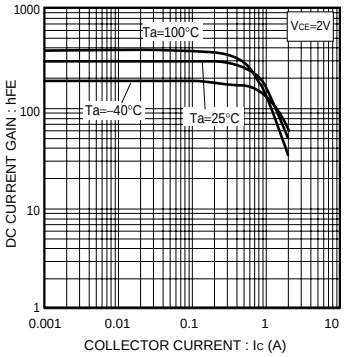


Fig.3 DC current gain vs. collector current

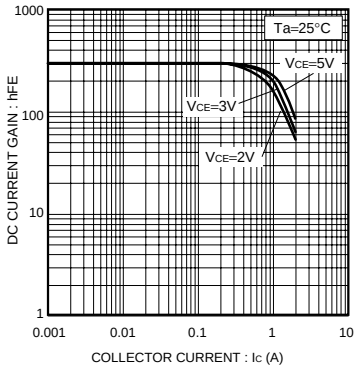


Fig.4 DC current gain vs. collector current

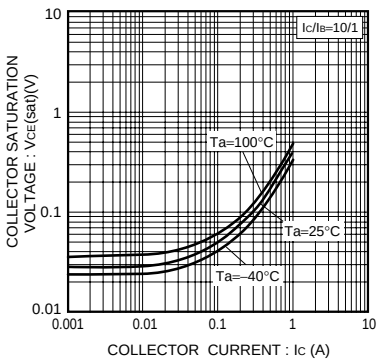


Fig.5 Collector-emitter saturation voltage vs. collector current

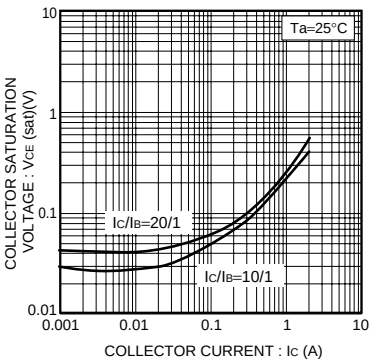


Fig.6 Collector-emitter saturation voltage vs. collector current

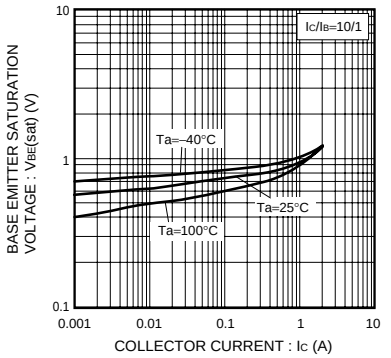


Fig.7 Base-emitter saturation voltage vs. collector current

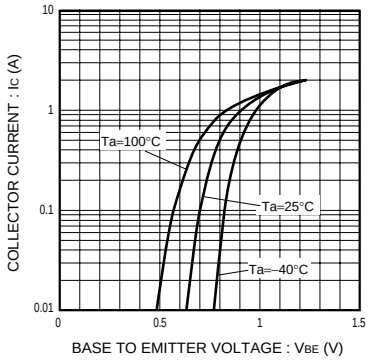


Fig.8 Ground emitter propagation characteristics

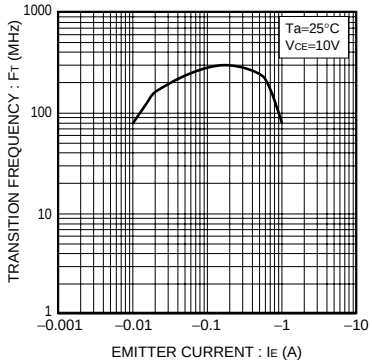


Fig.9 Transition frequency

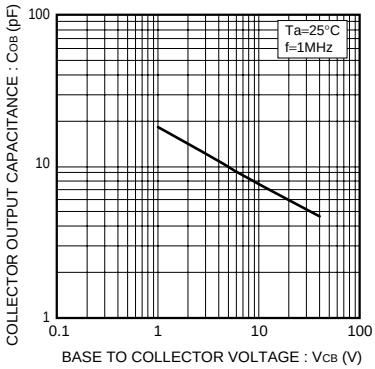
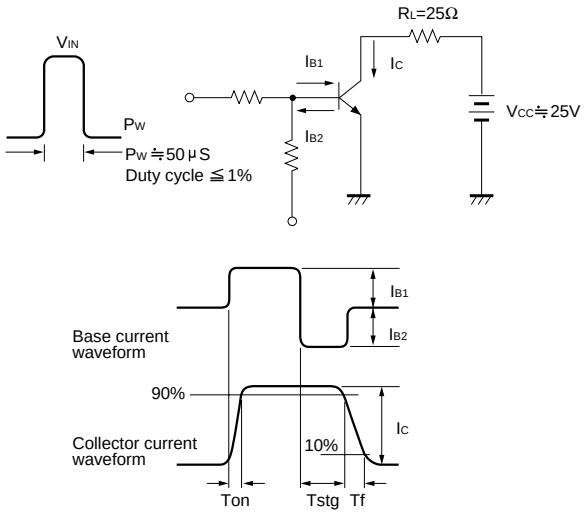


Fig.10 Collector output capacitance

●Switching characteristics measurement circuits



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